

# **isc Silicon NPN Power Transistor**

# 2SC3747

### DESCRIPTION

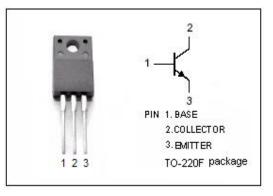
- Good Linearity of h<sub>FE</sub>
- · High Switching Speed
- Low Collector Saturation Voltage
- Complement to Type 2SA1470
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

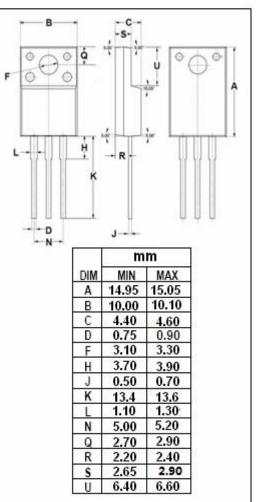
### **APPLICATIONS**

- · Inductance, lamp drivers
- · Inverters, converters
- · Power amplifiers
- High-speed switching applications.

SYMBOL	PARAMETER	VALUE	UNIT		
V <sub>CBO</sub>	Collector-Base Voltage	80	V		
V <sub>CEO</sub>	Collector-Emitter Voltage	60	V		
V <sub>EBO</sub>	Emitter-Base Voltage	5	V		
Ιc	Collector Current-Continuous	7	A		
I <sub>CM</sub>	Collector Current-Pulse	10	А		
Pc	Collector Power Dissipation @T <sub>c</sub> =25°C	25	W		
	Collector Power Dissipation @T <sub>a</sub> =25°C	2.0			
TJ	Junction Temperature	150	°C		
T <sub>stg</sub>	Storage Temperature	-55~150	°C		

## ABSOLUTE MAXIMUM RATINGS(T<sub>2</sub>=25°C)





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### **ELECTRICAL CHARACTERISTICS**

### Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	Ic= 1mA; R <sub>BE</sub> = ∞	60			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	80			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	5			V
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3.5A; I <sub>B</sub> = 0.175A			0.4	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 40V ; I <sub>E</sub> = 0			100	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V; I <sub>C</sub> = 0			100	μA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 1A ; V <sub>CE</sub> = 2V	70		280	
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A ; V <sub>CE</sub> = 5V		100		MHz

#### Switching times

t <sub>on</sub>	Turn-on Time		0.1	μs
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 3A , I <sub>B1</sub> = -I <sub>B2</sub> = 0.15A; R <sub>L</sub> = 6.67 Ω ; V <sub>CC</sub> = 20V	0.5	μ <b>S</b>
t <sub>f</sub>	Fall Time		0.1	μ <b>S</b>

### h<sub>FE</sub> Classifications

Q	R	s
70-140	100-200	140-280

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